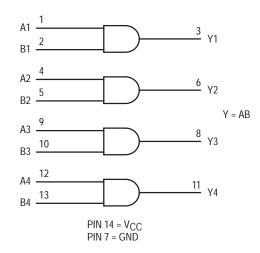
Quad 2-Input AND Gate

High-Performance Silicon-Gate CMOS

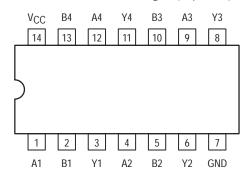
The MC74HC08A is identical in pinout to the LS08. The device inputs are compatible with Standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 24 FETs or 6 Equivalent Gates

LOGIC DIAGRAM



Pinout: 14-Lead Packages (Top View)





ON Semiconductor

http://onsemi.com



PDIP-14 N SUFFIX CASE 646



MARKING



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

WL or L = Wafer Lot YY or Y = Year WW or W = Work Week

FUNCTION TABLE

Inputs		Output
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

ORDERING INFORMATION

Device	Package	Shipping
MC74HC08AN	PDIP-14	2000 / Box
MC74HC08AD	SOIC-14	55 / Rail
MC74HC08ADR2	SOIC-14	2500 / Reel
MC74HC08ADT	TSSOP-14	96 / Rail
MC74HC08ADTR2	TSSOP-14	2500 / Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
ICC	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $\mbox{GND} \leq (\mbox{V}_{in} \mbox{ or } \mbox{V}_{out}) \leq \mbox{V}_{CC}.$

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

 $\label{problem} \mbox{Functional operation should be restricted to the Recommended Operating Conditions}.$

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			Vcc	V
TA	Operating Temperature, All Package Types			+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

DC CHARACTERISTICS (Voltages Referenced to GND)

			vcc	Guara	nteed Lim	nit	
Symbol	Parameter	Condition	V	–55 to 25°C	≤85°C	≤125°C	Unit
VIH	Minimum High-Level Input Voltage	$V_{Out} = 0.1V \text{ or } V_{CC} -0.1V$ $ I_{Out} \le 20 \mu A$	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
VIL	Maximum Low–Level Input Voltage	$V_{Out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{Out} \le 20\mu\text{A}$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
VOH	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{OUt} ≤ 20μΑ	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{array}{ c c c } \hline V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4 \text{mA} \\ & I_{out} \leq 4.0 \text{mA} \\ & I_{out} \leq 5.2 \text{mA} \\ \end{array} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{Out} ≤ 20μΑ	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$ \begin{aligned} V_{\text{in}} &= V_{\text{IH}} \text{ or } V_{\text{IL}} & & I_{\text{out}} \leq 2.4 \text{mA} \\ & I_{\text{out}} \leq 4.0 \text{mA} \\ & I_{\text{out}} \leq 5.2 \text{mA} \end{aligned} $	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
lin	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μА
Icc	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0μA	6.0	1.0	10	40	μА

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS ($C_L = 50pF$, Input $t_f = t_f = 6ns$)

		ν _{CC}	Guaranteed Limit			
Symbol	Parameter	V	–55 to 25°C	≤85°C	≤125°C	Unit
^t PLH [,] ^t PHL	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	·	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25° C, $V_{CC} = 5.0 \text{ V}$, $V_{EE} = 0 \text{ V}$	
C_{PD}	Power Dissipation Capacitance (Per Buffer)*	20	рF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

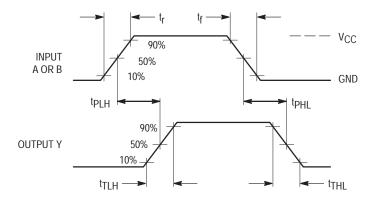
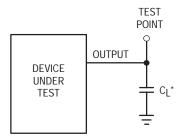


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

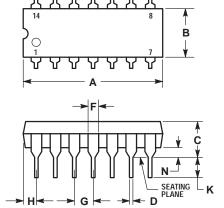
Figure 2. Test Circuit



Figure 3. Expanded Logic Diagram (1/4 of the Device)

PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE L



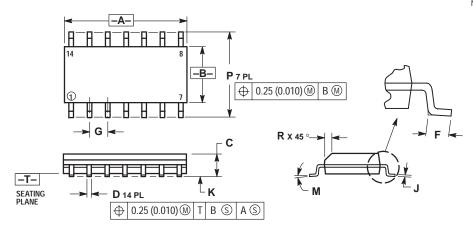


- NOTES:
 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION.
 2. DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEL.
 3. DIMENSION B DOES NOT INCLUDE MOLD

 - FLASH.
 4. ROUNDED CORNERS OPTIONAL

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300	BSC	7.62	BSC
M	0 °	10°	0°	10°
N	0.015	0.039	0.39	1.01

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE F



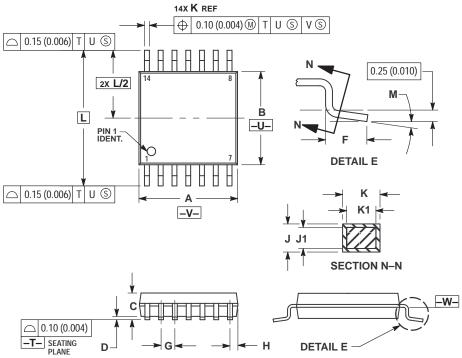
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI

- 1. DIMENSIONING AND TOLERANCING PER ANS Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWARD F. DAMBAR.
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE O**



- IES:
 DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH,
 PROTRUSIONS OR GATE BURRS. MOLD FLASH
 OR GATE BURRS SHALL NOT EXCEED 0.15
- OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007 0.010	
L	6.40		0.252 BSC	
M	0°	8°	0° 8°	



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